

KSP13/14

Darlington Transistor • Collector-Emitter Voltage: V_{CES}=30V • Collector Dissipation: P_C (max)=625mW



1. Emitter 2. Base 3. Collector

NPN Epitaxial Silicon Darlington Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	30	V
V _{CES}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	10	V
I _C	Collector Current	500	mA
P _C	Collector Dissipation	625	mW
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

Electrical Characteristics T_a =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CES}	Collector-Emitter Breakdown Voltage	I _C =100μA, I _B =0	30		V
I _{CBO}	Collector Cut-off Current	V _{CB} =30V, I _E =0		100	nA
I _{EBO}	Emitter Cut-off Current	V _{EB} =10V, I _C =0		100	nA
h _{FE}	* DC Current Gain : KSP13 : KSP14 : KSP13 : KSP14	V_{CE} =5V, I_{C} =10mA V_{CE} =5V, I_{C} =100mA	5K 10K 10K 20K		
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =100mA, I _B =0.1mA		1.5	V
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} =5V, I _C =100mA		2.0	V
f _T	Current Gain Bandwidth Product	V _{CE} =5V, I _C =10mA f=100MHz	125		MHz

^{*} Pulse Test: Pulse Width≤300µs, Duty Cycle≤2%

Typical Characteristics

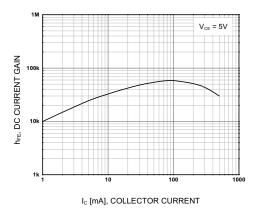


Figure 1. DC current Gain

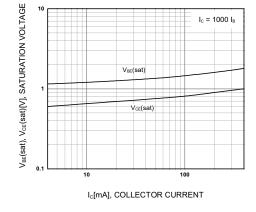


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

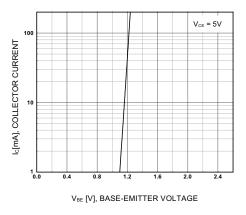


Figure 3. Base-Emitter On Voltage

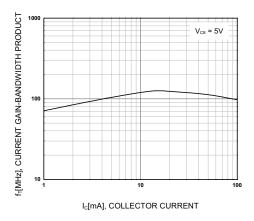
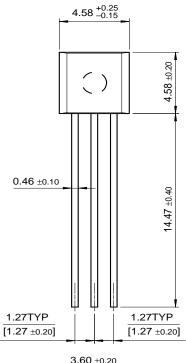


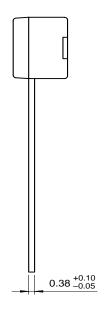
Figure 4. Current Gain Bandwidth Product

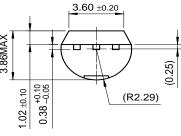
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Package Demensions

TO-92







Dimensions in Millimeters

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